Michel Vergnat

List of Publications by Year
in descending order

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151 papers	2,077 citations	279701 23 h-index	315616 38 g-index
152 all docs	152 docs citations	152 times ranked	1523 citing authors

#	Article	IF	Citations
1	Evidence of light-emitting amorphous silicon clusters confined in a silicon oxide matrix. Journal of Applied Physics, 2001, 89, 237-243.	1.1	118
2	Photoluminescence and electroluminescence of size-controlled silicon nanocrystallites embedded in SiO2 thin films. Journal of Applied Physics, 2005, 98, 046105.	1.1	86
3	Intense visible photoluminescence in amorphous SiOx and SiOx:H films prepared by evaporation. Applied Physics Letters, 1998, 72, 3157-3159.	1.5	79
4	Applying an improved phonon confinement model to the analysis of Raman spectra of germanium nanocrystals. Journal of Experimental and Theoretical Physics, 2014, 118, 65-71.	0.2	69
5	Structure and photoluminescence properties of evaporated GeOx thin films. Applied Physics Letters, 2006, 89, 011902.	1.5	62
6	Evolution with the annealing treatments of the photoluminescence mechanisms in a-SiNx:H alloys prepared by reactive evaporation. Journal of Applied Physics, 2007, 101, 123532.	1.1	61
7	Electron-paramagnetic-resonance study of the microscopic structure of the Si(001)-SiO2interface. Physical Review B, 1995, 52, R11599-R11602.	1.1	57
8	Magnetic and structural properties of iron nitride thin films obtained by argonâ€nitrogen reactive radioâ€frequency sputtering. Journal of Applied Physics, 1995, 77, 5309-5313.	1.1	56
9	Photoluminescence properties of size-controlled silicon nanocrystals at low temperatures. Journal of Applied Physics, 2009, 106, 023501.	1.1	51
10	Photoluminescence of Nd-doped SnO2 thin films. Applied Physics Letters, 2012, 100, .	1.5	50
11	Visible photoluminescence in amorphous SiOx thin films prepared by silicon evaporation under a molecular oxygen atmosphere. Applied Physics Letters, 2003, 82, 3877-3879.	1.5	49
12	Interpretation of the luminescence quenching in chemically etched porous silicon by the desorption of SiH3species. Applied Physics Letters, 1994, 65, 82-84.	1.5	48
13	Influence of the annealing treatments on the luminescence properties of SiOâˆ•SiO2 multilayers. Journal of Applied Physics, 2006, 100, 123504.	1.1	44
14	Visible photoluminescence in amorphous SiNx thin films prepared by reactive evaporation. Applied Physics Letters, 2000, 77, 3499-3501.	1.5	43
15	Strong visible photoluminescence in amorphous SiOx and SiOx:H thin films prepared by thermal evaporation of SiO powder. Journal of Luminescence, 1998, 80, 445-448.	1.5	41
16	Structure and photoluminescence properties of evaporated GeO[sub x]âˆ•SiO[sub 2] multilayers. Journal of Applied Physics, 2006, 100, 113106.	1.1	30
17	Structure and short-range order of vapour-deposited Si_{1âˆ’x}Sn_x amorphous alloys. The Philosophical Magazine: Physics of Condensed Matter B, Statistical Mechanics, Electronic, Optical and Magnetic Properties, 1985, 51, 327-336.	0.6	29
18	Improvement of the photoluminescence properties in a-SiNx films by introduction of hydrogen. Applied Physics Letters, 2001, 79, 2172-2174.	1.5	28

#	Article	IF	Citations
19	Formation of Ge and GeSi nanocrystals in GeO_x/SiO₂multilayers. Journal Physics D: Applied Physics, 2013, 46, 275305.	1.3	28
20	Structure and optical properties of amorphous SiOx thin films prepared by co-evaporation of Si and SiO. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2000, 69-70, 484-488.	1.7	27
21	Natural oxidation of annealed chemically etched porous silicon. Thin Solid Films, 1995, 255, 228-230.	0.8	26
22	Raman and photoluminescence spectroscopy of SiGe layer evolution on Si(100) induced by dewetting. Journal of Applied Physics, 2018, 123, .	1.1	26
23	Memristor effect in GeO[SiO2] and GeO[SiO] solid alloys films. Applied Physics Letters, 2019, 114, .	1.5	26
24	Effects of the amorphous-crystalline transition on the luminescence of quantum confined silicon nanoclusters. Europhysics Letters, 2004, 66, 674-679.	0.7	25
25	Structure and d.c. conductivity of amorphous Si1â^'xSnx alloys. Solid State Communications, 1984, 50, 237-242.	0.9	23
26	Evolution with annealing treatments of the size of silicon nanocrystallites embedded in a SiNx matrix and correlation with optical properties. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2003, 101, 186-189.	1.7	23
27	Thermal stability of titanium hydride thin films. Applied Physics Letters, 1994, 64, 1210-1211.	1.5	22
28	Influence of hydrogenation on the structure and visible photoluminescence of germanium oxide thin films. Journal of Luminescence, 2009, 129, 729-733.	1.5	22
29	Structural and Photoluminescence Properties of Evaporated SnO2 Thin Films Doped with Rare Earths. Energy Procedia, 2015, 84, 141-148.	1.8	21
30	Magnetic behavior ofFexSn1â^'xamorphous alloys near the critical composition. Physical Review B, 1983, 28, 1480-1489.	1.1	19
31	Interference effect in non-specular scattering from multilayers interpretation of the rocking curves. Solid State Communications, 1989, 71, 1045-1050.	0.9	19
32	Growth and characterization studies of Fe4N thin films prepared by ion beam assisted evaporation. Applied Physics Letters, 1995, 67, 430-432.	1.5	18
33	Influence of the annealing temperature on the photoluminescence of Er-doped SiO thin films. Journal of Applied Physics, 2007, 102, 053515.	1.1	18
34	Embedded Silicon Nanocrystals Studied by Photoluminescence and Raman Spectroscopies: Exciton and Phonon Confinement Effects. Journal of Physical Chemistry C, 2010, 114, 17344-17349.	1.5	18
35	Influence of the temperature on the photoluminescence of silicon clusters embedded in a silicon oxide matrix. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 382-387.	1.3	17
36	Structure and optical properties of SiN x : H films with Si nanoclusters produced by low-frequency plasma-enhanced chemical vapor deposition. Semiconductors, 2009, 43, 1514-1520.	0.2	17

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37	Optical properties of uniformly sized silicon nanocrystals within a single silicon oxide layer. Journal of Nanoparticle Research, 2013, 15, 1.	0.8	16
38	Low-angle neutron and x-ray scattering of hydrogenated and deuterated Mo/V superlattices. Physical Review B, 1994, 50, 11223-11226.	1.1	15
39	Densification of amorphous silicon prepared by hydrogenâ€ionâ€beamâ€assisted evaporation. Applied Physics Letters, 1996, 69, 1582-1584.	1.5	15
40	On the low-temperature synthesis of SWCNTs by thermal CVD. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 2268-2271.	1.3	15
41	Structure and infrared photoluminescence of GeSi nanocrystals formed by high temperature annealing of GeO_x/SiO₂multilayers. Materials Research Express, 2016, 3, 085019.	0.8	15
42	Resistive Switching in Non-Stoichiometric Germanosilicate Glass Films Containing Ge Nanoclusters. Electronics (Switzerland), 2020, 9, 2103.	1.8	15
43	Quantum Size Effects in Germanium Nanocrystals and Amorphous Nanoclusters in GeSixOy Films. Physics of the Solid State, 2020, 62, 492-498.	0.2	15
44	Luminescence efficiency at 1.5Î¼m of Er-doped thick SiO layers and Er-doped SiOâ•SiO2 multilayers. Applied Physics Letters, 2006, 89, 101920.	1.5	14
45	Negative and Positive Photoconductivity and Memristor Effect in Alloyed GeO[SiO] Films Containing Ge Nanoclusters. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000165.	1.2	14
46	Evidence of hydrogen modulation in Si/Si:H amorphous multilayers. Physical Review B, 1989, 40, 1418-1421.	1.1	13
47	Nitrogen stability measurements in sputtered iron nitride thin films by thermal desorption spectrometry. Solid State Communications, 1997, 102, 677-679.	0.9	13
48	Optical properties of tensile-strained and relaxed Ge films grown on InGaAs buffer. Journal of Applied Physics, 2014, 115, 053518.	1.1	13
49	Optical properties of Ce-doped SiO2 films: From isolated Ce3+ ions to formation of cerium silicate. Journal of Alloys and Compounds, 2015, 622, 358-361.	2.8	13
50	Indirect excitation of Er3+ ions in silicon nitride films prepared by reactive evaporation. Applied Physics Letters, 2010, 97, .	1.5	12
51	Preparation of hydrogenated amorphous silicon tin alloys. Revue De Physique AppliquÃ©e, 1987, 22, 1803-1808.	0.4	12
52	Antiferromagnetic order in a Dy/Er superlattice. Physical Review B, 1994, 49, 12274-12277.	1.1	11
53	Improvement of the stability under illumination of a-Si:H films elaborated by ion-beam-assisted evaporation using a hydrogenâ€“argon plasma. Journal of Applied Physics, 1998, 83, 1103-1106.	1.1	11
54	Optical phonons as a probe to determine both composition and strain in In x Al (1â^'x) As quantum dots embedded in an AlAs matrix. Europhysics Letters, 2014, 105, 16003.	0.7	11

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55	Ge nanocrystals formed by furnace annealing of Ge(x)[SiO2](1â^'x)films: structure and optical properties. Materials Research Express, 2017, 4, 075010.	0.8	11
56	Optical studies of bonding in coevaporated amorphous silicon-tin alloys. Physical Review B, 1989, 39, 3711-3719.	1.1	10
57	Local hydrogen environments in Gd1â^'xFexthin films amorphous alloys from effusion experiments. Applied Physics Letters, 1994, 64, 2084-2086.	1.5	10
58	Magnetic and structural properties of sputtered Feî—¸N thin films. Journal of Magnetism and Magnetic Materials, 1995, 140-144, 717-718.	1.0	10
59	Correlation between structure and photoluminescence in amorphous hydrogenated silicon nitride alloys. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 16, 445-449.	1.3	10
60	Light-emitting defects formed in GeO/SiO2 heterostructures with assistance of swift heavy ions. Journal of Luminescence, 2019, 207, 209-212.	1.5	10
61	Thermal desorption spectroscopy study of chemically etched porous silicon. Applied Surface Science, 1995, 89, 35-38.	3.1	9
62	Tunneling giant magnetoresistance in coevaporated Fex(SiO)1â^'x thin films. Journal of Applied Physics, 2000, 88, 6075-6077.	1.1	9
63	X-ray diffraction and MÃ¶ssbauer study of (Fe1â^'xNix)4N (0.2â‰¤xâ‰¤0.6) films. Journal of Alloys and Compounds, 2007, 440, 43-45.	2.8	9
64	Comparative study of the nonlinear optical properties of Si nanocrystals fabricated by eâ€beam evaporation, PECVD or LPCVD. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 969-973.	0.8	9
65	Direct and indirect excitation of Nd3+ ions sensitized by Si nanocrystals embedded in a SiO2 thin film. Journal of Applied Physics, 2011, 110, 113518.	1.1	9
66	Anomalous temperature dependence of photoluminescence in GeO x films and GeO x /SiO2 nano-heterostructures. JETP Letters, 2012, 95, 424-428.	0.4	9
67	Tailoring the surface density of silicon nanocrystals embedded in SiOx single layers. Journal of Applied Physics, 2013, 114, 233101.	1.1	9
68	Forming ability and stability of amorphous M x Sn 1â^'x alloys (M = V, Cr, Mn, Fe,Co, Ni, Cu). Journal of Non-Crystalline Solids, 1984, 61-62, 1243-1248.	1.5	8
69	Determination of Short-Range Motion of Hydrogen in Amorphous Silicon Multilayers by Low-Angle Neutron Scattering. Europhysics Letters, 1991, 14, 457-462.	0.7	8
70	Visible photoluminescence from chemically etched porous silicon: Influence of the surface state. Solid State Communications, 1994, 89, 683-686.	0.9	8
71	Magnetic structure of Tb films and Tb/Y superlattices. Journal of Magnetism and Magnetic Materials, 1995, 140-144, 771-772.	1.0	8
72	Hydrogen effusion from evaporated Si1â^'xSnx:H (0â‰¤xâ‰¤0.2) amorphous semiconductors. Applied Physics Letters, 1995, 66, 1647-1649.	1.5	8

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73	Influence of argon and hydrogen ions energy on the structure of a-Si:H prepared by ion-beam-assisted evaporation. Nuclear Instruments & Methods in Physics Research B, 1999, 147, 79-83.	0.6	8
74	Influence of the substrate temperature on the structure and the optical properties of amorphous Si:H thin films prepared by reactive evaporation. Thin Solid Films, 2002, 403-404, 153-156.	0.8	8
75	Structure and optical properties of amorphous silicon oxide thin films with different porosities. Journal of Non-Crystalline Solids, 2003, 320, 64-75.	1.5	8
76	Magnetic and transport properties of evaporated Fe/SiO multilayers. Journal of Applied Physics, 2004, 96, 1159-1164.	1.1	8
77	1.54Î¼m photoluminescence of Er-doped GeOx thin films. Journal of Applied Physics, 2007, 102, 106103.	1.1	8
78	Infrared photoluminescence from GeSi nanocrystals embedded in a germaniumâ€“silicate matrix. Journal of Experimental and Theoretical Physics, 2015, 121, 1076-1081.	0.2	8
79	Structural and optical study of Ce segregation in Ce-doped SiO1.5 thin films. Journal of Applied Physics, 2015, 118, 234308.	1.1	8
80	Influence of the barrier thickness on the photoluminescence properties of amorphous Si/SiO multilayers. Journal of Luminescence, 2005, 113, 64-68.	1.5	7
81	Study of the photoluminescence of amorphous and crystalline silicon clusters in SiOx thin films. Optical Materials, 2005, 27, 983-987.	1.7	7
82	Modification of germanium nanoclusters in GeO x films during isochronous furnace and pulse laser annealing. Technical Physics Letters, 2010, 36, 439-442.	0.2	7
83	Optical properties of a silicon-nanocrystal-based-microcavity prepared by evaporation. Optical Materials, 2011, 33, 1248-1251.	1.7	7
84	Some aspects of the precipitation of FeÎ± crystallites in the FePC amorphous alloy. Solid State Communications, 1985, 53, 191-195.	0.9	6
85	Structure and transport properties of amorphous SnxSi1-x alloys (0â‰¤xâ‰¤1) prepared by evaporation under an atomic hydrogen flow. Journal of Non-Crystalline Solids, 1991, 137-138, 907-910.	1.5	6
86	Study of the hydrogen stability in evaporated amorphous Si1âˆ’xSnx:H (0â‰¤xâ‰¤0.2) alloys by neutron scattering and exodiffusion measurements. Journal of Applied Physics, 1993, 73, 483-485.	1.1	6
87	Hydrogen diffusion and densification in amorphous silicon. Physical Review B, 1993, 47, 7584-7587.	1.1	6
88	Photoluminescence and electroluminescence of amorphous SiOx films prepared by reactive evaporation of silicon with oxygen. Optical Materials, 2005, 27, 1074-1078.	1.7	6
89	Observation of a nanoscale phase separation in blue-emitting Ce-doped SiO_{1.5} thin films. Journal of Materials Chemistry C, 2015, 3, 12499-12506.	2.7	6
90	Low-temperature photoluminescence properties of Nd-doped silicon oxide thin films containing silicon nanocrystals. Journal of Luminescence, 2017, 183, 311-314.	1.5	6

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91	Raman shifts and photoluminescence of the InSb nanocrystals ion beam-synthesized in buried SiO2 layers. Journal of Luminescence, 2018, 204, 656-662.	1.5	6
92	Infrared photoluminescence from GeO[SiO2] and GeO[SiO] solid alloy layers irradiated with swift heavy Xe ions. Journal of Luminescence, 2020, 223, 117238.	1.5	6
93	Experimental study of the dc conductivity mechanisms in amorphousSixSn1âˆ'xalloys. Physical Review B, 1988, 37, 8867-8874.	1.1	5
94	Evidence of hydrogen modulation in amorphous germanium prepared by reactive evaporation. Applied Physics Letters, 1993, 63, 2109-2111.	1.5	5
95	Observation of (100) surfaces in p-type porous silicon by electron paramagnetic resonance. Thin Solid Films, 1996, 276, 241-243.	0.8	5
96	Influence of the silicon nanocrystal size on the 1.54â€‚Î¼m luminescence of Er-doped SiO/SiO2 multilayers. Journal of Applied Physics, 2009, 105, 036101.	1.1	5
97	Photoluminescence properties of Nd-doped silicon oxide thin films containing silicon nanoparticles. Journal of Luminescence, 2014, 150, 35-39.	1.5	5
98	Photoluminescence properties of Ce³⁺ ions in Ceâ€‰doped SiO_{1.5} thin films containing Si nanocrystals. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 1630-1633.	0.8	5
99	Optical properties of GeO[SiO] and GeO[SiO2] solid alloy layers grown at low temperature. Optical Materials, 2021, 122, 111736.	1.7	5
100	Evidence for amorphous multilayered silicon obtained by deposition under modulated pressure of hydrogen. Journal of Applied Physics, 1988, 64, 4536-4537.	1.1	4
101	Experimental study of a pulsed microwave plasma assisted chemical vapour deposition of carbon nanotubes. Physica Status Solidi A, 2005, 202, 2079-2084.	1.7	4
102	MÃ¶ssbauer study of (Fe1âˆ'xCux)4N (0.05â©½xâ©½0.15) films. Physica B: Condensed Matter, 2007, 388, 180-182.	1.2	4
103	Preparation of dense, smooth and homogeneous amorphous silicon nitride films by nitrogen-ion-beam assisted evaporation. Journal Physics D: Applied Physics, 2008, 41, 175410.	1.3	4
104	Quasi-direct optical transitions in Ge nanocrystals embedded in GeO2 matrix. JETP Letters, 2009, 89, 76-79.	0.4	4
105	Phenomenological quantum confinement models for excitons and phonons applied to photoluminescence and Raman spectra of silicon nanocrystals. Physica Status Solidi (B): Basic Research, 2011, 248, 2724-2727.	0.7	4
106	Atomic scale investigation of Si and Ceâ€‰rich nanoclusters in Ceâ€‰doped SiO_{1.5} thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 1313-1316.	0.8	4
107	Direct Insight into Ce-Silicates/Si-Nanoclusters Snowman-Like Janus Nanoparticles Formation in Ce-Doped SiO_x Thin Layers. Journal of Physical Chemistry C, 2017, 121, 12447-12453.	1.5	4
108	Plasmonic and metallic optical properties of Au/SiO2 metal-insulator films. Journal of Applied Physics, 2017, 122, .	1.1	4

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109	On the Formation of IR-Light-Emitting Ge Nanocrystals in Ge:SiO2 Films. Semiconductors, 2018, 52, 1178-1187.	0.2	4
110	On the Formation of Amorphous Ge Nanoclusters and Ge Nanocrystals in GeSixOy Films on Quartz Substrates by Furnace and Pulsed Laser Annealing. Semiconductors, 2020, 54, 322-329.	0.2	4
111	Formation of SiP₂ Nanocrystals Embedded in SiO₂ from Phosphorus-Rich SiO_{1.5} Thin Films. Journal of Physical Chemistry C, 2020, 124, 7973-7978.	1.5	4
112	Influence of phosphorus on the growth and the photoluminescence properties of Si-NCs formed in P-doped SiO/SiO₂ multilayers. Nanoscale, 2021, 13, 19617-19625.	2.8	4
113	Formation of germanium nanocrystals and amorphous nanoclusters in GeSiOx films using electron beam annealing. Vacuum, 2022, 197, 110796.	1.6	4
114	Low angle polarized neutron diffraction from Tb/Fe multilayers. Physica B: Condensed Matter, 1992, 180-181, 489-491.	1.3	3
115	Homogeneous chemical etching of sand-blasted silicon substrates. Thin Solid Films, 1995, 255, 231-233.	0.8	3
116	Characterization of hydrogenated amorphous silicon prepared by ion beam assisted evaporation. Nuclear Instruments & Methods in Physics Research B, 1996, 112, 263-266.	0.6	3
117	MÃ¶ssbauer characterization of FeN thin films prepared by reactive evaporation. Thin Solid Films, 1996, 275, 251-253.	0.8	3
118	Photoluminescence of erbium in SiOxNy alloys annealed at high temperature. Journal of Alloys and Compounds, 2014, 593, 56-60.	2.8	3
119	Correlation between the nanoscale structure and the optical properties of Ce-doped SiO 1.5 thin films. Journal of Luminescence, 2017, 191, 88-91.	1.5	3
120	Polarized neutron reflection study of an Er/Fe multilayer. Journal of Magnetism and Magnetic Materials, 1994, 130, 305-312.	1.0	2
121	Thermal desorption spectrometry study of Si1â^'xGex:H amorphous alloys. Applied Surface Science, 1997, 119, 224-228.	3.1	2
122	Enhanced hydrogen stability in a-Si:H thin films evaporated under a flow of energetic argon ions. Applied Surface Science, 2002, 193, 175-179.	3.1	2
123	Magnetic and transport properties of annealed Fe(SiO) alloys. Journal of Magnetism and Magnetic Materials, 2004, 284, 165-171.	1.0	2
124	1.54Î¼m luminescence of Er-doped SiOx and GeOx thin films: A comparative study. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 146, 146-150.	1.7	2
125	Scanning-probe-induced local decomposition of solid germanium monoxide films: The nano-pattering of germanium. Journal of Surface Investigation, 2009, 3, 773-780.	0.1	2
126	Temperature Dependence of the Photoluminescence Intensity in Si3+xN4:H Films with Amorphous Si Nanoclusters: Evidence for Two Processes Involved in the Nonradiative Relaxation of Photoexcitations. ECS Transactions, 2009, 25, 35-42.	0.3	2

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127	STRUCTURE AND LOCAL ORDER IN AMORPHOUS Si1-x SNx SEMI-CONDUCTOR ALLOYS. Journal De Physique Colloque, 1985, 46, C8-287-C8-291.	0.2	2
128	Light sensitive memristors based on GeSixOy films with Ge nanoclusters. , 2022, , .		2
129	Preparation and structure of amorphous semiconductor hydrogenated tin. Applied Physics Letters, 1990, 57, 2300-2301.	1.5	1
130	Modulation of Hydrogen in Amorphous Materials. Key Engineering Materials, 1991, 40-41, 311-318.	0.4	1
131	Magnetic and Structural Properties of Iron Nitride thin Films Obtained by Argon-Nitrogen Reactive Radio-Frequency Sputtering. Materials Research Society Symposia Proceedings, 1995, 384, 103.	0.1	1
132	Influence of the SiO thickness on the photoluminescence properties of Er-doped SiO/SiO2 multilayers. Journal of Luminescence, 2006, 121, 238-241.	1.5	1
133	Towards spectroscopy of a few silicon nanocrystals embedded in silica. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 998-1001.	1.3	1
134	The decomposition mechanism of metastable solid GeO film. , 2009, , .		1
135	Laser pulse crystallization and optical properties of Si/SiO₂and Si/Si₃N₄multilayer nano-heterostructures. Proceedings of SPIE, 2013, , .	0.8	1
136	GeSi nanocrystals formed by high temperature annealing of GeO/SiO2 multilayers: structure and optical properties. , 2016, , .		1
137	Vibrational and Light-Emitting Properties of Si/Si1âˆ’xSnx Heterostructures. JETP Letters, 2019, 109, 368-371.	0.4	1
138	Neutron diffraction measurements of the kinetics of crystallization of amorphous FePC and FEF3, xHF. Physica B: Physics of Condensed Matter & C: Atomic, Molecular and Plasma Physics, Optics, 1986, 136, 42-44.	0.9	0
139	Modulation and thermal stability of hydrogen in amorphous silicon. Physica B: Condensed Matter, 1991, 170, 141-145.	1.3	0
140	Some applications of low angle neutron scattering to hydrogenated amorphous silicon multilayers. Physica B: Condensed Matter, 1992, 180-181, 471-473.	1.3	0
141	Polarized neutron scattering from multilayers. Neutron News, 1995, 6, 26-30.	0.1	0
142	Stability of Nitrogen in Sputtered Iron Nitride thin films and Multilayers. Materials Research Society Symposia Proceedings, 1997, 475, 309.	0.1	0
143	Photoluminescence of undoped and erbium-doped SiO/SiO/sub 2/ multilayers. , 0, , .		0
144	Influence of oxygen content on the 1.54Î¼m luminescence of Er-doped amorphous SiOx thin films. Physica E: Low-Dimensional Systems and Nanostructures, 2009, 41, 1059-1062.	1.3	0

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145	Plasmon-enhanced luminescence from silicon nanocrystals. , 2013, , .		0
146	Plasmonic Effects in Metal-Semiconductor Nanostructures. By Alexey A. Toropov and Tatiana V. Shubina. Oxford University Press, 2015. Pp. 384. Price GBP 75.00. ISBN 9780199699315.. Acta Crystallographica Section B: Structural Science, Crystal Engineering and Materials, 2015, 71, 579-581.	0.5	0
147	Evolution of Silicon and Hydrogen Bonding in Silicon-Rich Nitride Films Prepared by Plasma-Enhanced Chemical Vapor Deposition and Annealed Under High Pressure. Nanoscience and Nanotechnology Letters, 2013, 4, 364-368.	0.4	0
148	Modulation and thermal stability of hydrogen in amorphous silicon. , 1991, , 141-145.		0
149	MÃ¶ssbauer characterization of FeN thin films prepared by reactive evaporation. , 1996, , 251-253.		0
150	Characterization of hydrogenated amorphous silicon prepared by ion beam assisted evaporation. , 1996, , 263-266.		0
151	Luminescent properties of GeOx thin films and GeO/SiO2 heterostructures modified with swift heavy ions. , 2019, , .		0